PMCM440VNE

12 V, N-channel Trench MOSFET

7 April 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a 4 bumps Wafer Level Chip-Size Package (WLCSP) using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Ultra small package: 0.78 × 0.78 × 0.35 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	12	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	5	Α
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	57	67	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
A1	G	gate	1 2	D I
A2	S	source	A () ()	
B1	D	drain		G A A
B2	S	source	В	T N
			Transparent top view WLCSP4 (OL- PMCM440VNE)	S 017aaa255

6. Ordering information

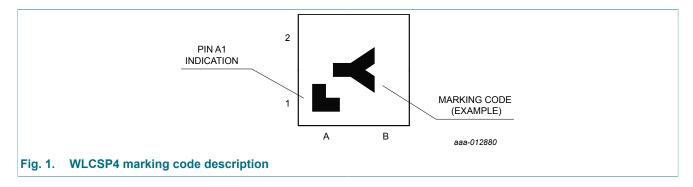
Table 3. Ordering information

Type number	Package	Package				
	Name	Description	Version			
PMCM440VNE	WLCSP4	WLCSP4: wafer level chip-size package; 4 bumps (2 x 2)	OL- PMCM440VNE			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMCM440VNE	M



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	12	V
V_{GS}	gate-source voltage			-8	8	٧
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	5	Α
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	3.9	Α
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	15.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	400	mW
			[1]	-	1300	mW
		T _{sp} = 25 °C		-	12500	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain	n diode		'	'	'	,
I _S	source current	T _{amb} = 25 °C	[1]	-	1.1	Α

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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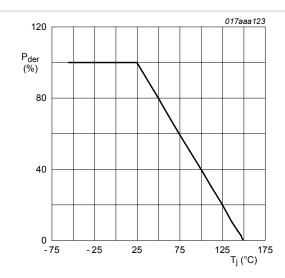


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

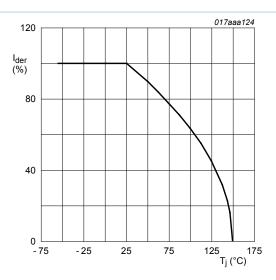


Fig. 3. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

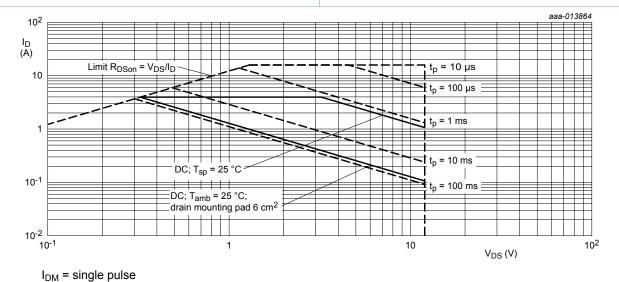


Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uily a)	thermal resistance		[1]	-	250	300	K/W
	from junction to ambient		<u>[2]</u>	-	70	85	K/W
			[3]	-	85	100	K/W
		in free air; t ≤ 5 s	<u>[3]</u>	-	50	60	K/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		_	5	10	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain, 4-layer, 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

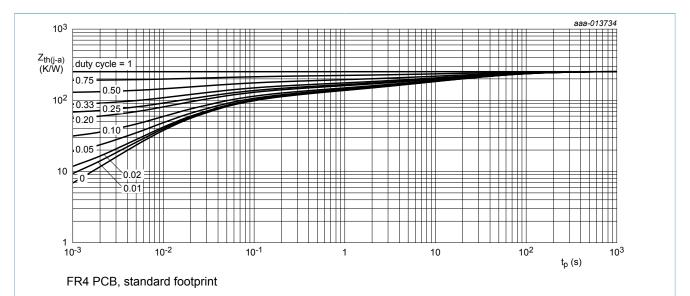


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

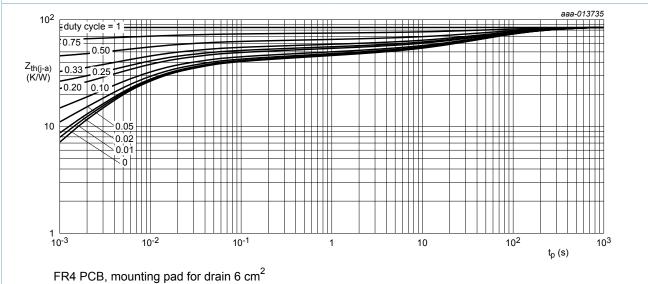


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	12	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.6	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 12 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	5	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-5	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	200	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-200	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 3 A; T _j = 25 °C	-	57	67	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 3 A; T _j = 150 °C	-	71	83	mΩ
		V _{GS} = 2.5 V; I _D = 3 A; T _j = 25 °C	-	66	88	mΩ
		V _{GS} = 1.8 V; I _D = 1 A; T _j = 25 °C	-	77	110	mΩ
		V _{GS} = 1.5 V; I _D = 0.1 A; T _j = 25 °C	-	90	130	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 6 \text{ V}; I_D = 3 \text{ A}; T_j = 25 \text{ °C}$	-	17	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	5.4	-	Ω
Dynamic c	haracteristics		'			
Q _{G(tot)}	total gate charge	$V_{DS} = 6 \text{ V}; I_D = 3 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	5.5	8.2	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.43	-	nC
Q_{GD}	gate-drain charge		-	1.5	-	nC
C _{iss}	input capacitance	V _{DS} = 6 V; f = 1 MHz; V _{GS} = 0 V;	-	360	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	160	-	pF
C _{rss}	reverse transfer capacitance		-	140	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 6 \text{ V}; I_D = 3 \text{ A}; V_{GS} = 4.5 \text{ V};$	-	6.3	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	27	-	ns
t _f	fall time		-	17	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain o	Source-drain diode						
V_{SD}	source-drain voltage	I _S = 1.1 A; V _{GS} = 0 V; T _j = 25 °C		-	0.7	1.2	V

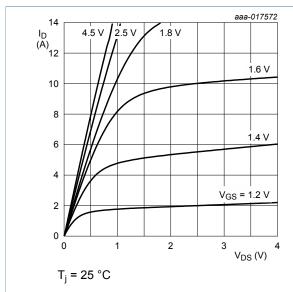
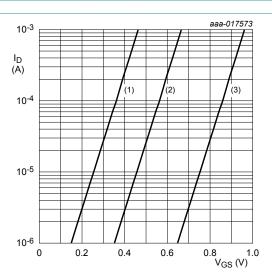


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values



 $T_i = 25 \,^{\circ}C; \, V_{DS} = 5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage

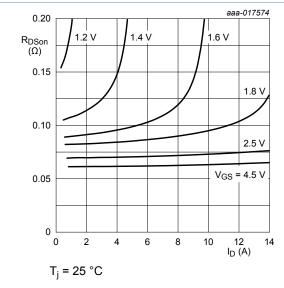


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

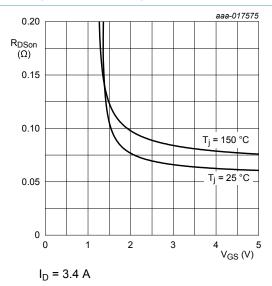


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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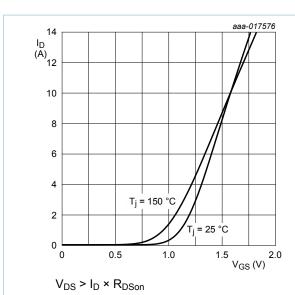


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

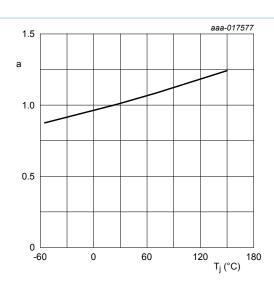
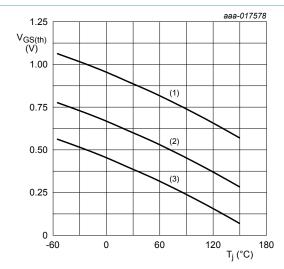


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

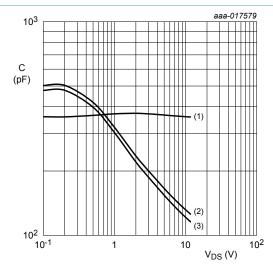
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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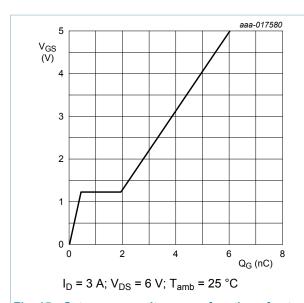


Fig. 15. Gate-source voltage as a function of gate charge; typical values

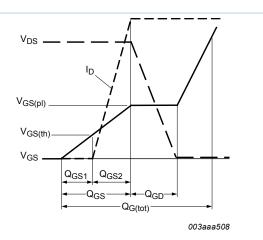


Fig. 16. MOSFET transistor: Gate charge waveform definitions

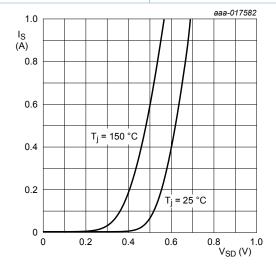
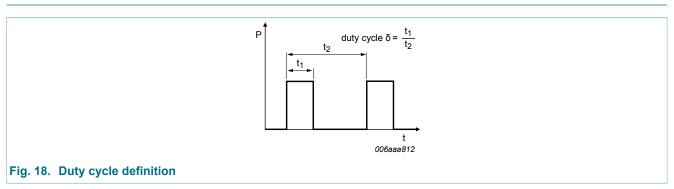


Fig. 17. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

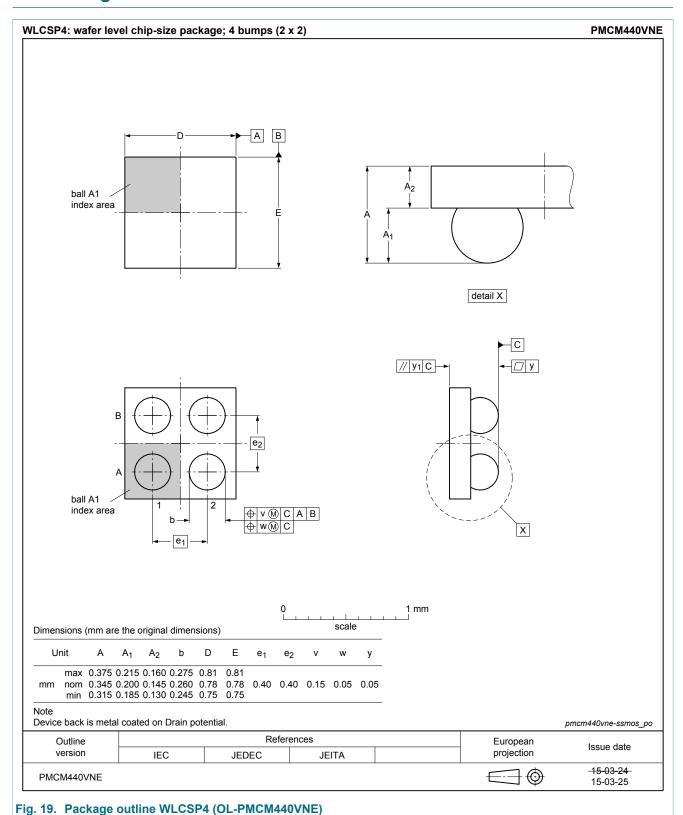


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12. Package outline



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13. Soldering

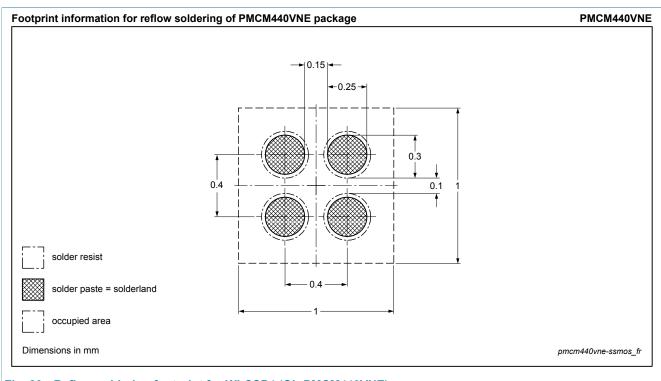


Fig. 20. Reflow soldering footprint for WLCSP4 (OL-PMCM440VNE)

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMCM440VNE v.1	20150407	Product data sheet	-	-

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15. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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